REASUNOS

瑞森網店　　官方微信

REASUNOS SEMICONDUCTOR TECHNOLOGY(GUANGDONG) CO.,LTD.
瑞森半導體科技(廣東)有限公司

China·Operation·Center （中國大陸運營中心）
4th Floor, B2 Tianan Cyber Park, Nancheng District, Dongguan City,
Guangdong Province, China.
廣東省東莞市南城區黄金路一號天安數碼城B2棟4樓
T +86-769–88766788 F +86-769–88766787 E sales1@reasunos.com

Taiwan Design Team （臺灣研發團隊）
5th Floor, No.5, Technology Road, Science-based Industrial Park,
Hsinchu, Taiwan
臺灣新竹市科學園區科技路5號5樓

Your Professional Semiconductor Partner

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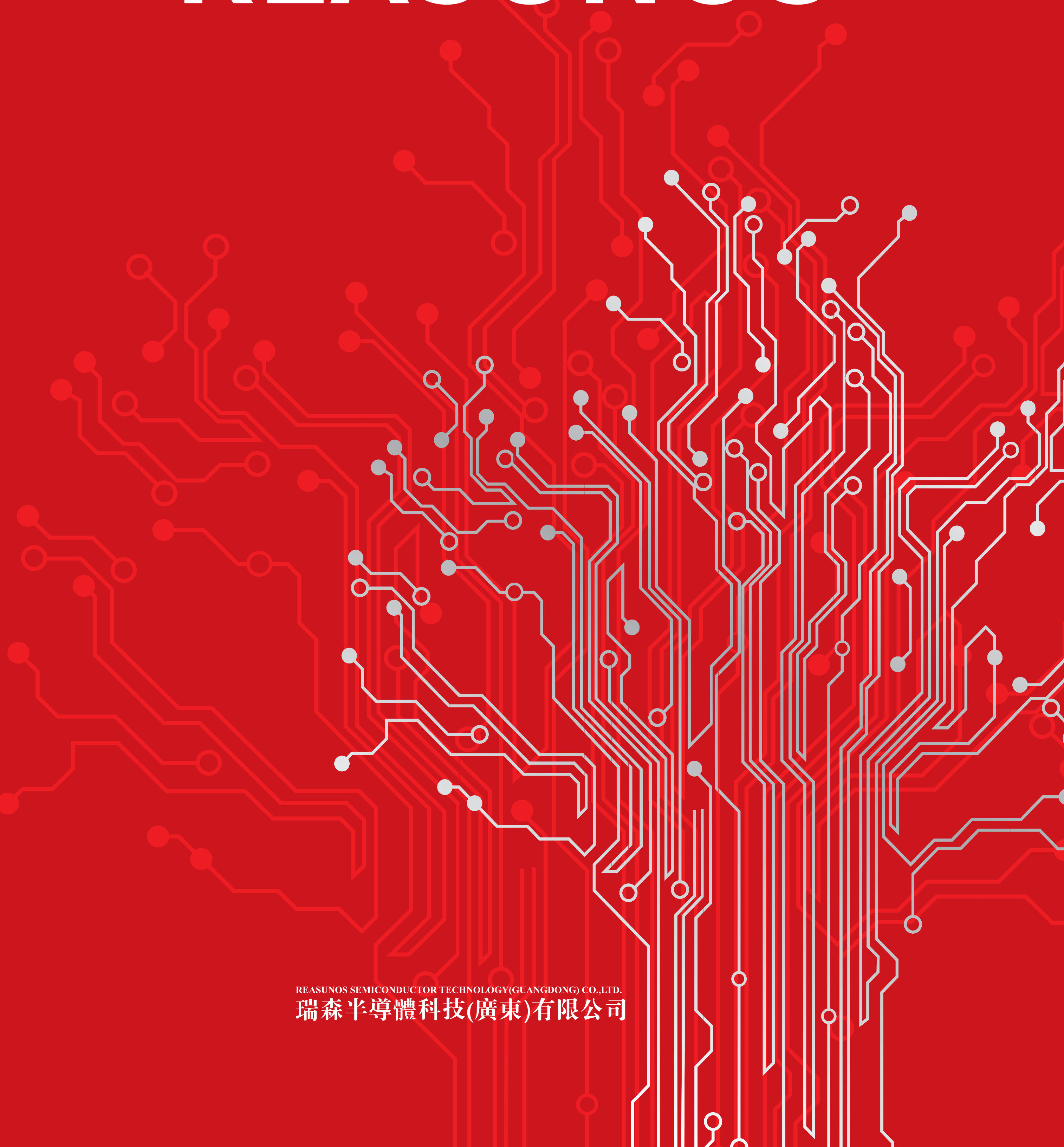

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REASUNOS

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ABOUT US

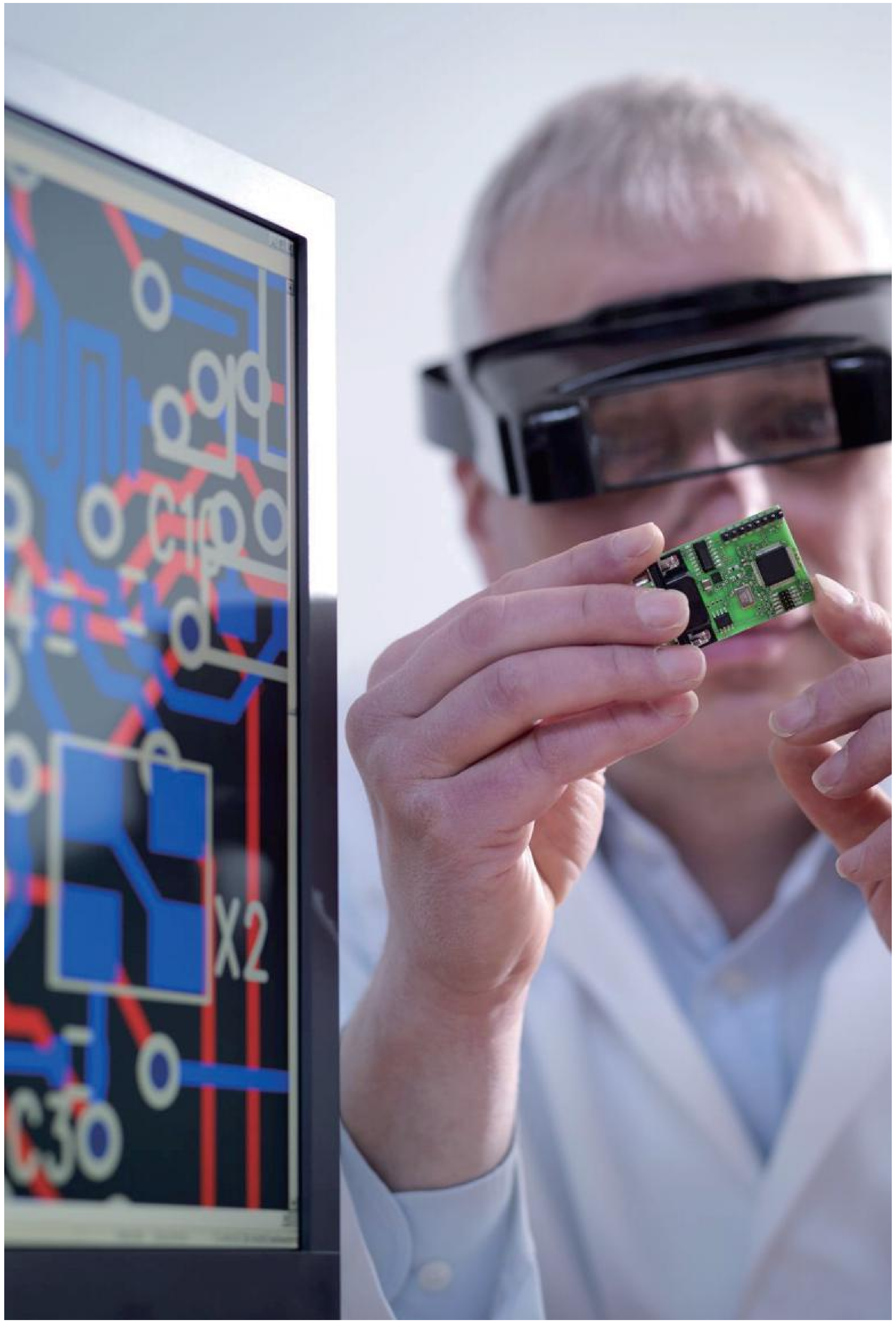
REASUNOS
Semiconductor

Reasunos Semiconductor Technology Co., Ltd start from 2007, it's a high technology enterprise which specializing in product design and marketing on Power Semiconductor. The professional R & D team mainly come from Taiwan, Japan and China mainland . The Chinese operating center is located in Dongguan Tian'an Cyber Park which it's national science and technology industry innovation center.

Our Core Products are including SiC MOSFET, SiC Schottky Barrier Diode, Super Junction MOSFET, High Voltage MOSFET, Low Voltage MOSFET, Embedded FRD HV MOS, IGBT, Low VF Schottky Diode, series of Diode etc.

With strong R & D experience and manufacturing capacity, Reasunos gained many Intellectual Property, provide more than 500KK excellent performance's semiconductor to the market every year. And gained RoHS & REACH environmental certification as well. The product sells at home and abroad.

Looking forward to the future, Reasunos will connect to the market trend closely, develop more competitive power discrete, IC and system solutions for our customers.



VISION

Product Concept

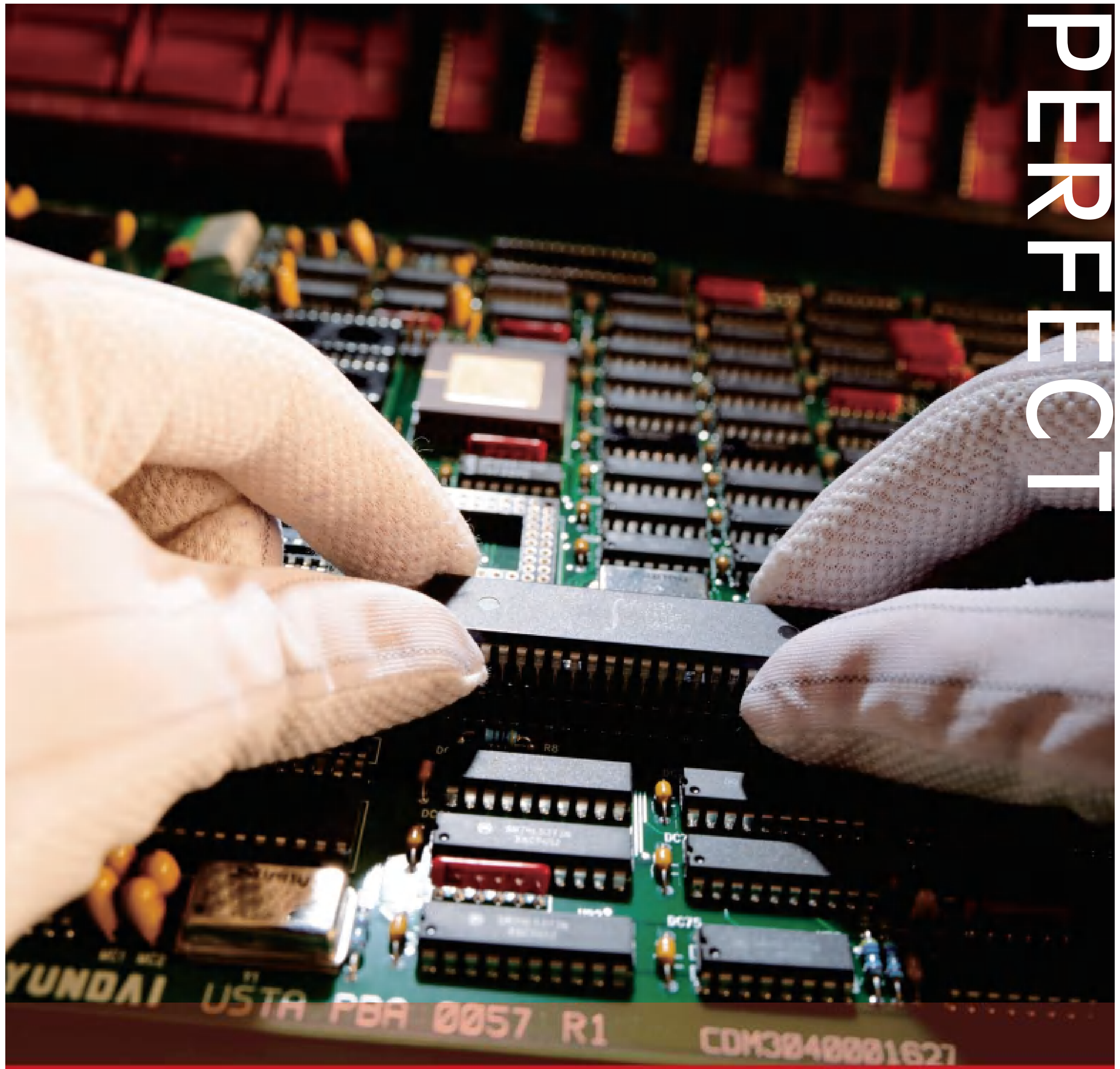
R&D:Technical innovation and prominence
Mass Production:
Adherence to first sample approval and consistency.

Vision

We pursue to be a prominent brand of Power Semiconductor and a leading role in the industry.

Mission

To provide Power Semiconductor with competitive advantages and good service to our customers.
To build an enabling platform for our employees to realize their value.
Strive to maximize investment returns for our partners.



Continuous R&D Innovations

Achieve the leader-ship in the market

LED Driver IC

Advantages: High power factor, High efficiency, Ultra low-flicker, Primary side control, Cost saving

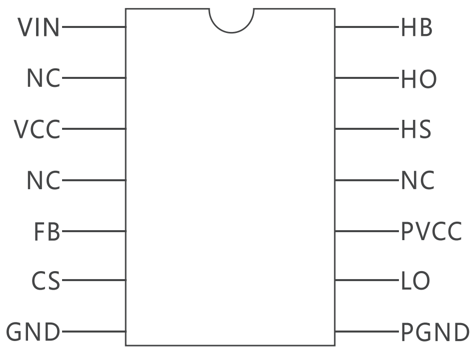
Applications: Constant-current LED driver, LLC resonance control

Product Model: RSC6105S RSC6107S RSC6112S RSC6120S

Features:

- Ultra-low flicker constant current regulation
- LLC topology with integrated half bridge driver
- Automatic dead time control
- Integrated 2mA high voltage starting circuit
- Extremely low output current ripple<2%
- Output power up to 100W
- Short circuit protection
- Open circuit protection
- Thermal shutdown protection
- SOP-14 package

Package way



Patent certificate

No.	Name	Funtion
1	VIN	High voltage enable input
2	NC	Pin
3	VCC	Power
4	NC	Pin
5	FB	Voltage feedback input
6	CS	Current sampling input
7	GND	Ground
8	PGND	Power Ground
9	LO	Half axle driver low side grid output
10	PVCC	Power supply
11	NC	Pin
12	HS	Half bridge driver high side ground
13	HO	Half bridge driver high side grid output
14	NB	Half bridge driver high side power

SiC MOSFET

Advantages: High speed switching with low capacitances, High blocking voltage with low RDS(on)
Applications:Solar Inverters, High Voltage DC/DC Converters, Motor Drivers, Switch Mode Power Supplies, UPS

No.	Product	Type	I_D(A)	V_{DSS}(V)	R_{DS}(on)		Package
					Typ(mΩ)	Max(mΩ)	
1	RSM065050T	N	52	650	50	65	TO-220
2	RSM065050W	N	52	650	50	65	TO-247
3	RSM120030W	N	80	1200	30	40	TO-247
4	RSM120050W	N	60.5	1200	50	62	TO-247
5	RSM120060W	N	41	1200	60	80	TO-247
6	RSM120080W	N	35.5	1200	80	120	TO-247
7	RSM120120W	N	20	1200	120	160	TO-247
8	RSM120160W	N	18	1200	160	200	TO-247
9	RSM120240W	N	10	1200	240	320	TO-247
10	RSM1701K0W	N	3.4	1700	1000	1400	TO-247

Note: Package T TO-220;D TO-252;MD TO-251 Short Pin;W TO-247;

Remark: Not all the products are listed,Please contact us if you have any other specification.

SiC Schottky Barrier Diode

Advantages: Zero reverse recovery current,High temperature operation,High frequency
Applications:PFC,Solar/Wind Inverters,Industrial Motor Drivers,Charge Block for Electrical Cars,Electrical Household Appliances,UPS

No.	Product	Electrical Characteristics(T_A=25℃)				Package
		Forward Voltage	Forward Current	Reverse Current	Reverse Voltage	
		V_F(V) Typ.	I_F(A)	I_R(uA)Typ.	V_R(V)	
1	RSS06065A	1.5	6	1	650	TO-220-2L
2	RSS06065D	1.5	6	1	650	TO-252
3	RSS08065A	1.42	8	1	650	TO-220-2L
4	RSS08065D	1.42	8	1	650	TO-252
5	RSS10065A	1.4	10	1	650	TO-220-2L
6	RSS10065D	1.4	10	1	650	TO-220-2L
7	RSS20065K	1.4	20	1	650	TO-247-3L
8	RSS30065W	1.5	30	2	650	TO-247-2L
9	RSS60065K	1.5	60	2	650	TO-247-3L
10	RSS06120A	1.55	6	1	1200	TO-220-2L
11	RSS08120D	1.55	8	1	1200	TO-252
12	RSS10120A	1.55	10	1	1200	TO-220-2L
13	RSS10120K	1.55	10	1	1200	TO-247-3L
14	RSS15120W	1.55	15	1.5	1200	TO-247-2L
15	RSS20120W	1.6	20	3	1200	TO-247-2L
16	RSS20120K	1.55	20	1	1200	TO-247-3L
17	RSS30120K	1.55	30	1.5	1200	TO-247-3L
18	RSS40120K	1.6	40	3	1200	TO-247-3L
19	RSS25170W	1.6	25	2	1700	TO-247-2L

Note: Note: Package A TO-220-2L;D TO-252;MD TO-251 Short Pin;W TO-247-2L;K TO-247-3L;

Remark: Not all the products are listed,Please contact us if you have any other specification.

Reasunos had established strict and completed quality management system to ensure the product quality.

High Voltage MOSFET

Advantages: Extremely Low R_{DS}(on), Better junction capacitor, High thermal performance
Application:LED Driver, Small Household Appliances, Industrial Switching Power Supplies etc.

No.	Product	Type	I_D(A)	V_{DSS}(V)	R_{DS}(on)		Package
					Typ(Ω)	Max(Ω)	
1	RS2N65*	N	2	650	4.10	4.80	TO-220F/252/251
2	RS4N65*	N	4	650	2.10	2.60	TO-220F/252/251
3	RS5N65*	N	5	650	1.90	2.40	TO-220F/252/251
4	RS6N65*	N	6	650	1.65	1.88	TO-220F/252/251
5	RS7N65*	N	7	650	1.10	1.40	TO-220F/252/251
6	RS8N65F	N	8	650	1.10	1.30	TO-220F
7	RS9N65D	N	9	650	0.85	0.95	TO-252
8	RS10N65F	N	10	650	0.68	0.85	TO-220F
9	RS12N65F	N	12	650	0.56	0.72	TO-220F
10	RS16N65F	N	16	650	0.45	0.55	TO-220F
11	RS20N65F	N	20	650	0.35	0.45	TO-220F
12	RS4N60*	N	4	600	1.80	2.20	TO-220F/252/251
13	RS7N60*	N	7	600	0.96	1.20	TO-220F/252/251
14	RS10N60F	N	10	600	0.60	0.78	TO-220F
15	RS12N60F	N	12	600	0.55	0.72	TO-220F
16	RS12N60F(A)	N	12	600	0.48	0.60	TO-220F
17	RS20N60*	N	20	600	0.30	0.42	TO-220F/3P
18	RS840*	N	8	500	0.68	0.85	TO-220/TO-220F/252
19	RS9N50*	N	9	500	0.70	0.85	TO-220F/252
20	RS10N50F	N	10	500	0.60	0.75	TO-220F
21	RS13N50F	N	13	500	0.42	0.52	TO-220F
22	RS13N50F(A)	N	13	500	0.37	0.45	TO-220F
23	RS15N50F	N	15	500	0.35	0.42	TO-220F
24	RS15N50F(A)	N	15	500	0.33	0.40	TO-220F
25	RS18N50*	N	18	500	0.27	0.32	TO-220F/TO-247
26	RS18N50(A)*	N	18	500	0.22	0.32	TO-220F/TO-247
27	RS20N50*	N	20	500	0.20	0.30	TO-220F/TO-247
28	RS30N50W	N	30	500	0.08	0.10	TO-247

Note: * means many Package type such as F TO-220F;D TO-252;MD TO-251 Short Pin;W TO-247;P TO-3P;

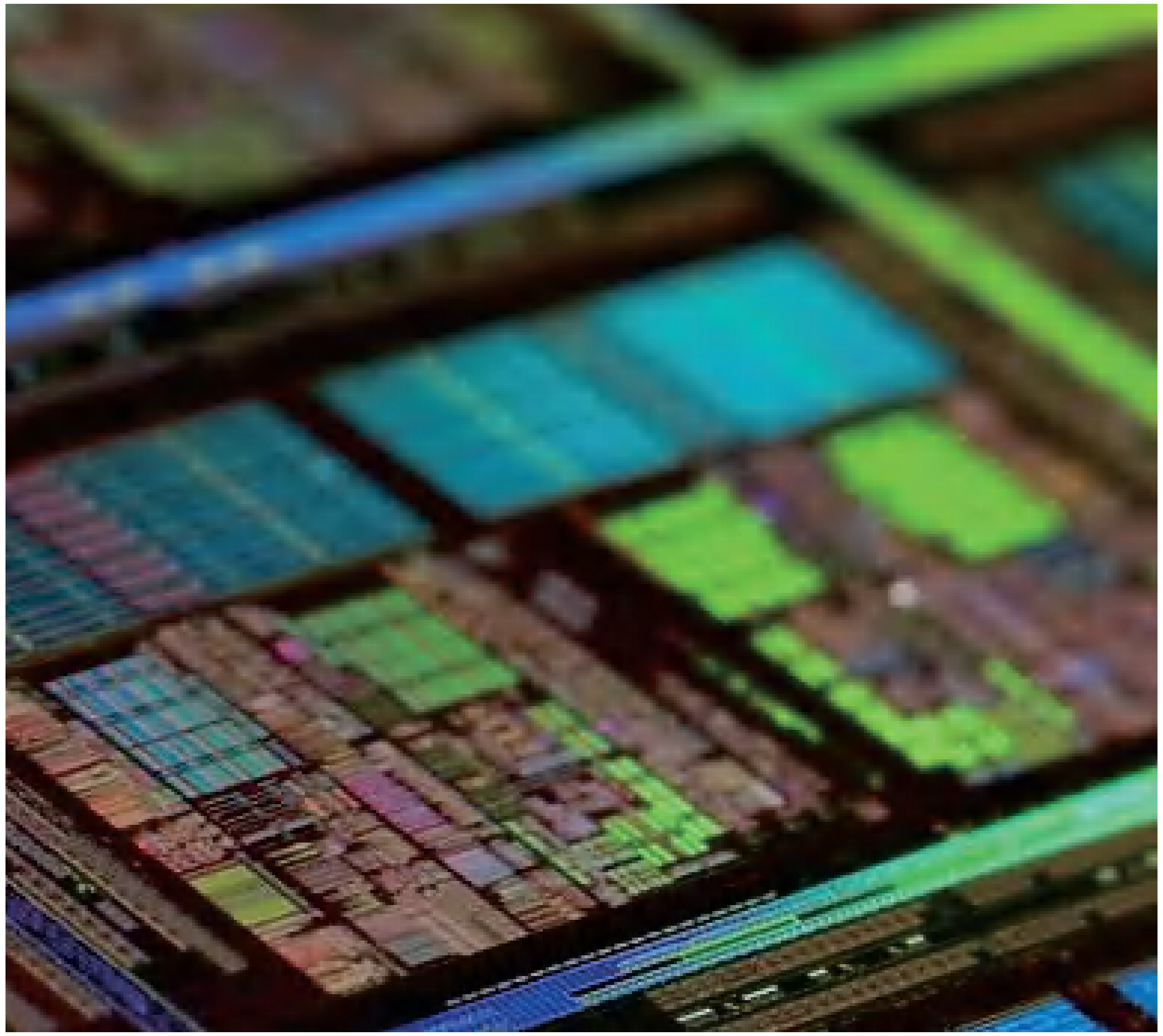
Remark: The Part No. with A, which can replace the international brand;

Ultrahigh Voltage MOSFET

Advantages: Ultra-High Voltage,Low R_{DS}(on), High thermal performance
Advantages:AC/DC Switching Power, LED Lighting,Industrial Application,Electric Power System

No.	Product	Type	I_D(A)	V_{DSS}(V)	R_{DS}(on)		Package
					Typ(Ω)	Max(Ω)	
1	RS4N70*	N	4	700	2.5	2.7	TO-220F/252/251
2	RS6N70*	N	6	700	1.3	1.6	TO-220F/252/251
3	RS11N70F	N	11	700	0.7	0.85	TO-220F
4	RS18N70F	N	18	700	0.45	0.55	TO-220F
5	RS4N80F	N	4	800	3	3.6	TO-220F
6	RS8N80F	N	8	800	1.3	1.5	TO-220F
7	RS10N80*	N	10	800	0.92	1.15	TO-220F/TO-3P
8	RS12N80*	N	12	800	0.67	0.8	TO-220F/TO-3P
9	RS4N90F	N	4	900	3	3.5	TO-220F
10	RS9N90*	N	9	900	1	1.2	TO-220F/TO-3P
11	RS11N90P	N	11	900	0.75	0.96	TO-3P
12	RS4N100F	N	4	1000	3.9	4.5	TO-220F
13	RS6N100F	N	6	1000	1.2	1.5	TO-220F
14	RS8N120W	N	8	1200	1.3	1.6	TO-247
15	RS4N150W	N	4	1500	4.5	6	TO-247

Remark: Not all the products are listed,Please contact us if you have any other specification.



Multi-EPI Super Junction MOSFET

Advantages: Low on-resistance and low conduction losses,Small package,Ultra Low Gate Charge cause lower driving requirements
Application: Power Factor Correction(PFC),Switched Mode Power Supplies(SMPS),Uninterruptible Power Supply(UPS)

No.	Product	Type	I_D(A)	V_{DSS}(V)	R_{DS}(on) Typ(mΩ)	R_{DS}(on) Max(mΩ)	Package
1	RSU7N65*	N	7	650	530	600	TO-220F/251/252
2	RSU11N65*	N	11	650	380	420	TO-220F/251/252
3	RSU12N65*	N	11.5	650	300	360	TO-220F/251/252
4	RSU15N65F	N	15	650	240	260	TO-220F
5	RSU18N65F	N	18	650	220	250	TO-220F
6	RSU20N65*	N	21	650	150	170	TO-247/220F
7	RSU47N65W	N	47	650	62	70	TO-247
8	RSU76N65W	N	76	650	35	40	TO-247
9	RSU76N65W(FRD)	N	76	650	39	44	TO-247

Note: * means many Package type such as F TO-220F;D TO-252;MD TO-251 Short Pin;W TO-247;P TO-3P;

Remark: Not all the products are listed,Please contact us if you have any other specification.

Embedded FRD HV MOS

Advantages: Integrate fast recovery diode;Reverse time 57-200nS;Including all current range:3A-25A,Voltage:500V-700V；Improved dv/dt capability
Applications: Motor Controls;Switch Mode Power Supply (SMPS);Power Factor Correction (PFC)

No.	Product	Type	I_D(A)	V_{DSS}(V)	R_{DS}(on) Typ(Ω)	R_{DS}(on) Max(Ω)	Diode Trr(nS)	Package
1	RSF5N50*	N	5	500	1.50	1.85	61	TO-220F/252/251
2	RSF7N50F	N	7	500	1.10	1.30	87	TO-220F
3	RSF8N50F	N	8	500	0.80	0.95	100	TO-220F
4	RSF13N50F	N	13	500	0.52	0.62	107	TO-220F
5	RSF15N50F	N	15	500	0.43	0.50	127	TO-220F
6	RSF25N50F	N	25	500	0.28	0.35	150	TO-220F
7	RSF4N60*	N	4	600	2.30	2.70	83	TO-220F/252/251
8	RSF6N60F	N	6	600	1.70	2.00	87	TO-220F
9	RSF7N60F	N	7	600	1.10	1.30	100	TO-220F
10	RSF10N60F	N	10	600	0.75	0.85	107	TO-220F
11	RSF12N60F	N	12	600	0.63	0.75	127	TO-220F
12	RSF6N70*	N	6	700	1.50	1.80	100	TO-220F/252/251

Note: * means many Package type such as F TO-220F;D TO-252;MD TO-251 Short Pin;W TO-247;P TO-3P;

Remark: Not all the products are listed,Please contact us if you have any other specification.

Low Voltage MOSFET

Advantages: Extremely Low RDS(on), Better junction capacitor,More efficient

Applications:
Wireless Charger, Quick Charger, Motor Driver, DC/DC Converter, High-Frequency Switching and Synchronous Rectification

No.	Product	Type	I_D(A)	V_{DSS}(V)	R_{DS}(on)		Package
					Typ(mΩ)	Max(mΩ)	
1	RS2301E	P	−3.4	−20	50	65	SOT-23
2	RS2302E	N	4	20	21	27	SOT-23
3	RS3415E	P	-4	-20	38	48	SOT-23
4	RS20N90D	N	90	20	2.8	4	TO-252
5	RS3401E	P	-4.2	-30	48	55	SOT-23
6	RS3400E	N	5.8	30	28	35	SOT-23
7	RS4435	P	-11	-30	18	20	SOP-8
8	RS30N24D	N	24	30	/	25	TO-252
9	RS30N60*	N	60	30	/	9	TO-220/TO-252
10	RS30N86D	N	86	30	3.6	5	TO-252
11	RS30N100D	N	100	30	4	5.5	TO-252
12	RS40N120*	N	120	40	2.8	3.3	TO-220/TO-252
13	RS2310E	N	3	60	/	100	SOT-23
14	RS60N40D	N	40	60	16	20	TO-252
15	RS60N80*	N	80	60	10	12	TO-220/TO-252
16	RS60N100T	N	100	60	5.5	6.6	TO-220
17	RS60N150T	N	150	60	3.3	4	TO-220
18	RS100N10D	N	10	100	/	120	TO-252
19	RS100N20D	N	20	100	45	55	TO-252
20	RS100N57T	N	57	100	13	16.5	TO-220
21	RS100N100T	N	100	100	9.9	13	TO-220
22	RS100N135T	N	135	100	3.7	4.5	TO-220

Note: * means many Package type such as F TO-220F;D TO-252;MD TO-251 Short Pin;W TO-247;P TO-3P;

Remark: Not all the products are listed,Please contact us if you have any other specification.

IGBT

Advantages: Switch fast,High input resistance,Small control power,Low VF,Conduction high current,Small wastage,
Enhance avalanche resistance energy

Applications:
Induction Heating(Induction Cooker, Rice Cooker),Air condition,Electric welding machine,Motor control,Uninterruptible Power,Industrial Application Supply(UPS),Inverters,Industrial Application

No.	Product	IC(A) Tc=100℃	VCES(V)	VCE(Sat)(V) (Typ)	VGE(th) (Typ)	Tf(nS) (Typ)	Package
1	RSG15N65F	15	650	1.65	5	60	TO-220F
2	RSG20N65F	20	650	1.9	5	60	TO-220F
3	RSG30N65W	30	650	1.9	4.6	140	TO-247
4	RSG60N65W	60	650	1.85	5	165	TO-247
5	RSG15N120W	15	1200	1.7	6	330	TO-247
6	RSG25N120W	25	1200	1.65	6	200	TO-247
7	RSG40N120W	40	1200	2	5.8	230	TO-247

Remark: Not all the products are listed,Please contact us if you have any other specification.

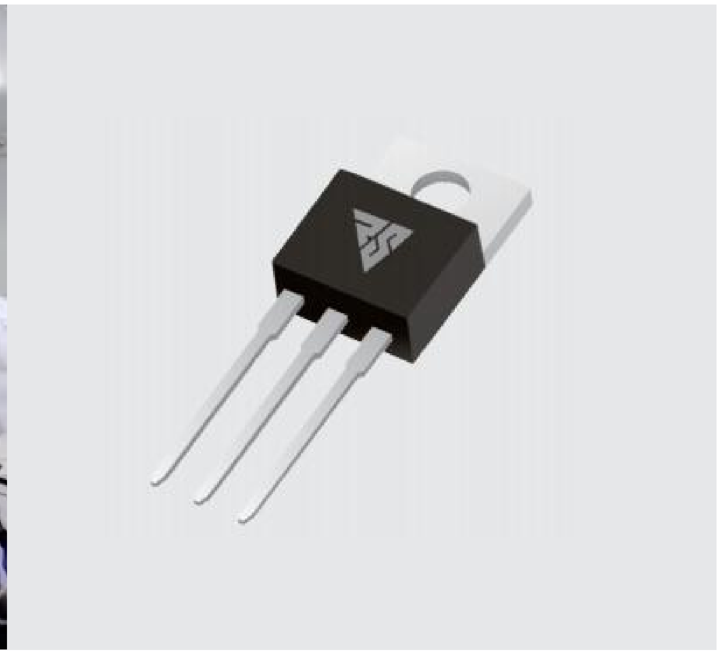
Low VF Schottky Diode

Advantages: Low VF, Small Leakage

Applications: Display Power Supplies, Notebook Power Supplies, Chargers etc

No.	Product	Io(A)	VR(V)	Electrical Characteristics(TA=25℃)		Package
				Forward Voltage	Reverse Current	
				VF(V) Max.	IR(mA) Max.	
1	MBR1045LCT	10	45	0.46	0.10	TO-220AB
2	MBR10100LCT	10	100	0.72	0.10	TO-220AB
3	MBR10200LCT	10	200	0.89	0.20	TO-220AB
4	MBR2045LCT	20	45	0.52	0.10	TO-220AB
5	MBR2060LCT	20	60	0.55	0.10	TO-220AB
6	MBR20100LCT	20	100	0.70	0.10	TO-220AB
7	MBR20200LCT	20	200	0.89	0.10	TO-220AB
8	MBR20300LCT	20	300	0.89	0.10	TO-220AB
9	MBR3045LCT	30	45	0.53	0.10	TO-220AB
10	MBR30100LCT	30	100	0.73	0.30	TO-220AB
11	MBR30200LCT	30	200	0.89	0.30	TO-220AB
12	MBR30300LCT	30	300	0.92	0.30	TO-220AB

Note: MBR means TO-220AB, we can also provide ITO-220 which product name using MBRF instead



Schottky Diode

Advantages: Low VF, Small Leakage, Cost-Effective

Applications: Adapters, Display Power Supplies, Notebook Power Supplies, Chargers etc

No.	Product	Io(A)	VR(V)	Electrical Characteristics(TA=25℃) Forward Voltage VF(V) Max.	Reverse Current IR(mA) Max.	Package
1	MBR10100CT	10	100	0.85	0.20	TO-220AB
2	MBR10150CT	10	150	0.87	0.20	TO-220AB
3	MBR10200CT	10	200	0.92	0.20	TO-220AB
4	MBR1645CT	16	45	0.65	0.20	TO-220AB
5	MBR2045CT	20	45	0.6	0.20	TO-220AB
6	MBR2060CT	20	60	0.78	0.20	TO-220AB
7	MBR20100CT	20	100	0.85	0.20	TO-220AB
8	MBR20150CT	20	150	0.9	0.20	TO-220AB
9	MBR20200CT	20	200	0.95	0.20	TO-220AB
10	MBR3045CT	30	45	0.65	0.20	TO-220AB
11	MBR30100CT	30	100	0.88	0.20	TO-220AB
12	MBR30150CT	30	150	0.88	0.20	TO-220AB
13	MBR30200CT	30	200	0.9	0.20	TO-220AB
14	MBR40100CT	40	100	0.85	0.20	TO-220AB
15	MBR40200CT	40	200	0.9	0.20	TO-220AB
16	MBR40200PT	40	200	0.9	0.20	TO-247
17	MBR40200PTS	40	200	0.9	0.20	TO-247S
18	MBRF30100VCT	30	100	0.73	0.20	ITO-220
19	MBR4060CT	40	60	0.75	0.20	TO-220AB
20	MBR3060PTS	30	60	0.75	0.20	TO-247S
21	MBR30100PTS	30	100	0.85	0.20	TO-247S
22	MBR4060PTS	40	60	0.75	0.20	TO-247S
23	MBR40100PTS	40	100	0.85	0.20	TO-247S

Note: MBR means TO-220AB, PTS means TO-247 short pins, we can also provide ITO-220 which product name using MBRF instead

Remark: Not all the products are listed,Please contact us if you have any other specification.

REASUNOS

高新技术企业

证书

中国半导体行业协会

会员证

单位:瑞森半导体科技(广东)有限公司

二〇一九年度